

CMOS Pixel Sensors designed for the STAR-PXL

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- coll. with IRFU-Saclay -

CERN – 29 May 2011

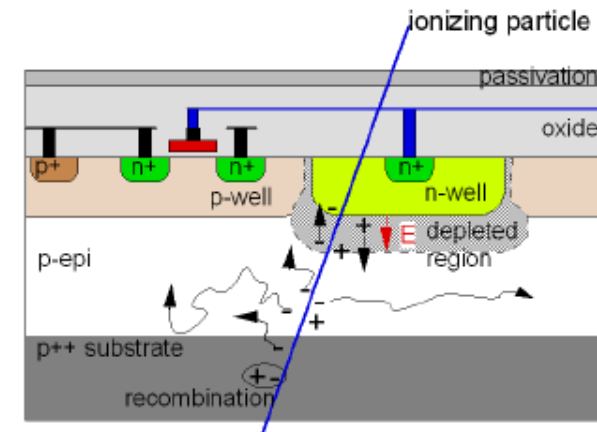
Contents

- *Basic features of CMOS sensors*
 - ✧ general remarks on highly pixelated and thin sensors
 - ✧ generic aspects of existing MIMOSA sensors
- *Status of sensor realisation*
 - ✧ sensor architecture
 - ✧ main outcome of sensor prototyping
 - ✧ preliminary lab test results of ULTIMATE sensors
- *Summary*

CMOS Pixel Sensors: State of the Art

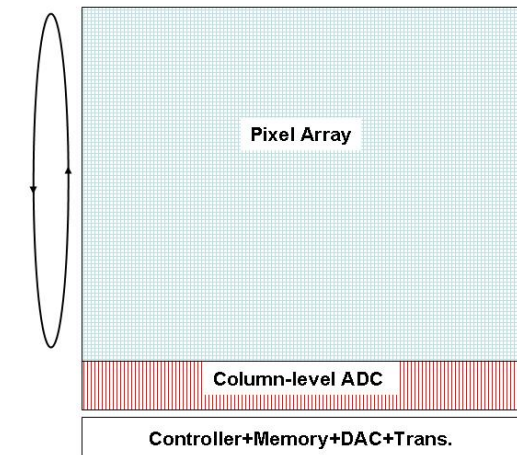
- **Prominent features of CMOS pixel sensors:**

- ✧ high granularity \Rightarrow excellent (micronic) spatial resolution
- ✧ very thin (signal generated in 10-20 μm thin epitaxial layer)
- ✧ signal processing μ -circuits integrated on sensor substrate
 \Rightarrow impact on downstream electronics (\Rightarrow cost)



- **Organisation of MIMOSA sensors:**

- ✧ manufactured in 0.35 μm OPTO process
- ✧ signal sensing and analog processing in pixel array
- ✧ mixed and digital circuitry integrated in chip periphery
- ✧ read-out in rolling shutter mode
(pixels grouped in columns read out in //)
 \Rightarrow impact on power consumption



Granularity versus Speed

- **Impact of high granularity:**

- ✳ large number of pixels \Rightarrow handicap for read-out speed of the full pixel array

- ✳ **but:** slow down of detector read-out frequency compensated by accuracy

- \hookrightarrow single point resolution and material budget :

- improved neighbouring hit separation on each detector layer

- improved track extrapolation accuracy during track reconstruction from layer to layer

- effect enhanced by small material budget

- strategy option: connect CMOS pixels sensors to 2-layer fast&thick detector

- ✳ **global effect :** improved track reconstruction capability in high density conditions

- \Rightarrow data rate handling capability not really downgraded (but track rec. SW needs to be adapted)

- **Illustration with CMOS pixels ($20 \times 20 \mu m^2$) :**

- ✳ $>$ 60 times smaller than ATLAS pixels ($50 \times 425 \mu m^2$)

- ✳ \gtrsim O(10-100) times more accurate track extrapolation for hit search

- \Rightarrow \sim **3 ordres of magnitude improvement in hit rate handling capability**

- \hookrightarrow single CMOS pixel layer in a tracker does not provide all added value of granular & thin sensors

- \hookrightarrow large particle rate does not necessarily imply priority to r.o. speed

CMOS Pixel Sensors: General Remarks

- **Intrinsic limitations of technology :**

- * very thin sensitive volume \Rightarrow impact on signal magnitude
- * standard process sensitive volume almost undepleted \Rightarrow impact on radiation tolerance & speed
- * commercial fabrication (parametres) \Rightarrow not optimised for charged particle detection
 \Rightarrow impact on sensing performances and radiation tolerance

- **Limitations of the fabrication process retained for ULTIMATE:**

- * only 4 ML \Rightarrow rolling shutter sequencer in 350 μm wide side band
- * feature size \Rightarrow restricted nb of transistors in the pixel
- * oxide thickness (from feature size) \Rightarrow weakens the tolerance to ionising radiation
- * double-well technology \Rightarrow restricted circuitry inside pixel

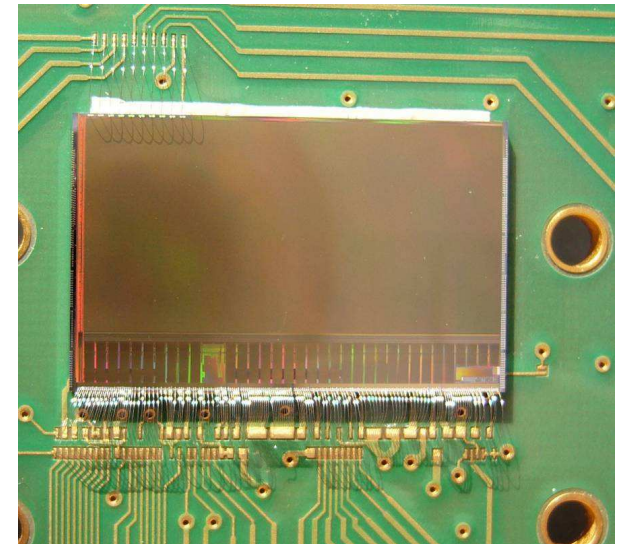
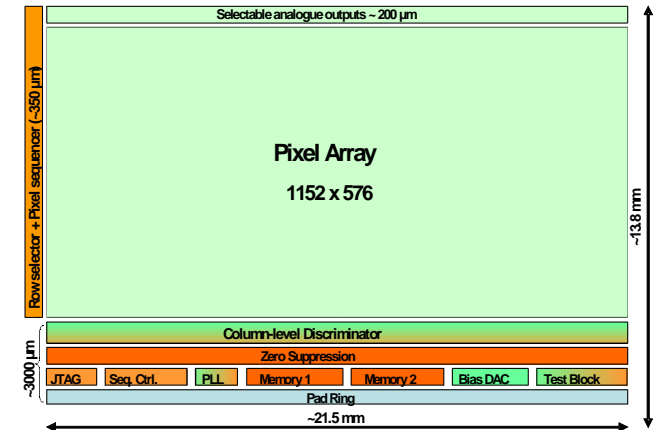
- **Limitations due to the STAR environment :**

- * limited cooling \Rightarrow power consumption is a concern (consequences on SNR, alignment)
- * limited cooling \Rightarrow reduced noise performance, in particular after irradiation (though not critical)

CMOS Pixel Sensors: State of the Art

- Main characteristics of MIMOSA sensor equipping EUDET BT:

- * $0.35 \mu m$ process with high-resistivity epitaxial layer
(coll. with IRFU/Saclay)
- * column // architecture with in-pixel amplification (CDS)
and end-of-column discrimination, followed by \emptyset
- * active area: 1152 columns of 576 pixels ($21.2 \times 10.6 \text{ mm}^2$)
- * pitch: $18.4 \mu m \rightarrow \sim 0.7$ million pixels
charge sharing $\Rightarrow \sigma_{sp} \lesssim 4 \mu m$
- * $t_{r.o.} \lesssim 100 \mu s$ ($\sim 10^4$ frames/s)
 \Rightarrow suited to $> 10^6$ part./ cm^2/s
- * $\sim 250 \text{ mW}/\text{cm}^2$ power consumption (fct of N_{col})



MIMOSA-26: Functionality Implementation

CMOS 0.35 μm OPTO technology
 Chip size : 13.7 x 21.5 mm²

- Pixel array: 576 x 1152, pitch: 18.4 μm
- Active area: $\sim 10.6 \times 21.2 \text{ mm}^2$
- In each pixel:
 - Amplification
 - CDS (Correlated Double Sampling)

- Testability: several test points implemented all along readout path
 - Pixels out (analogue)
 - Discriminators
 - Zero suppression
 - Data transmission

- Row sequencer
- Width: $\sim 350 \mu\text{m}$

- 1152 column-level discriminators
 - offset compensated high gain preamplifier followed by latch

- Zero suppression logic

- Reference Voltages Buffering for 1152 discriminators

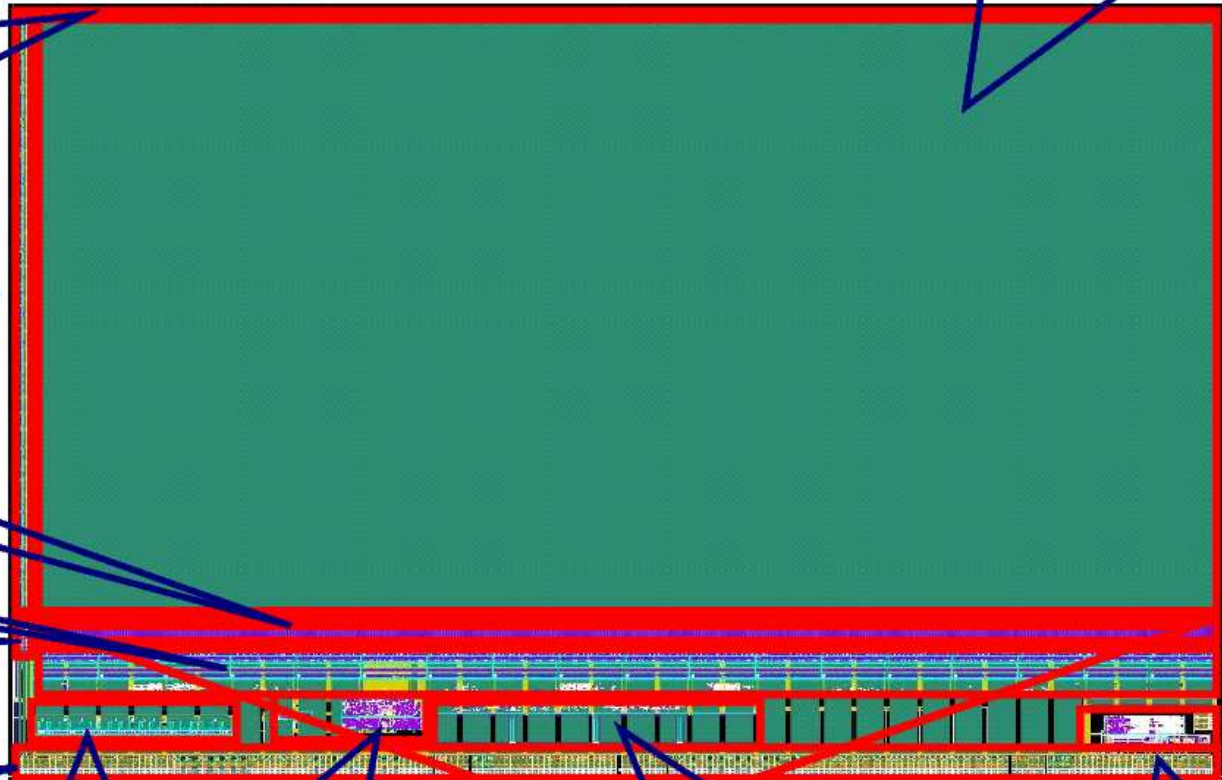
- I/O Pads
- Power supply Pads
- Circuit control Pads
- LVDS Tx & Rx

- Current Ref.
- Bias DACs

- Readout controller
- JTAG controller

- Memory management
- Memory IP blocks

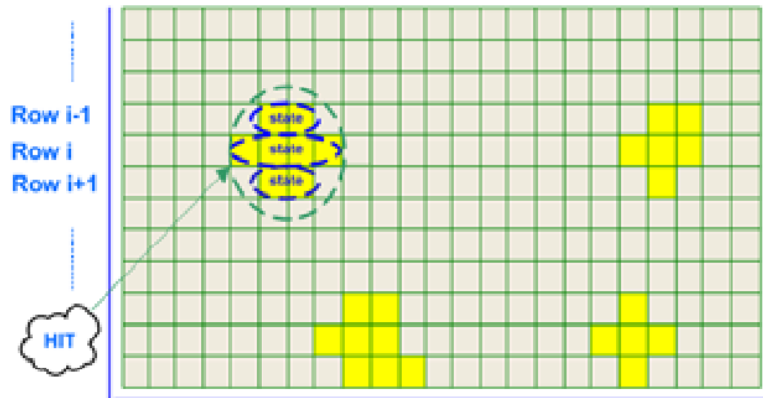
- PLL, 8b/10b optional



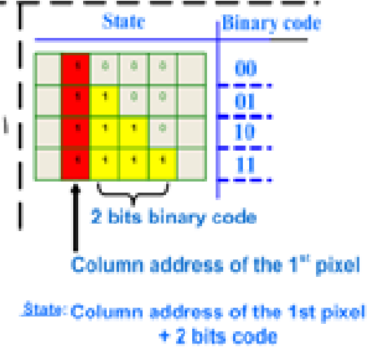
courtesy of Ch. Hu-Guo / TWEPP-2010

MIMOSA-26 Zero-Suppression Logic

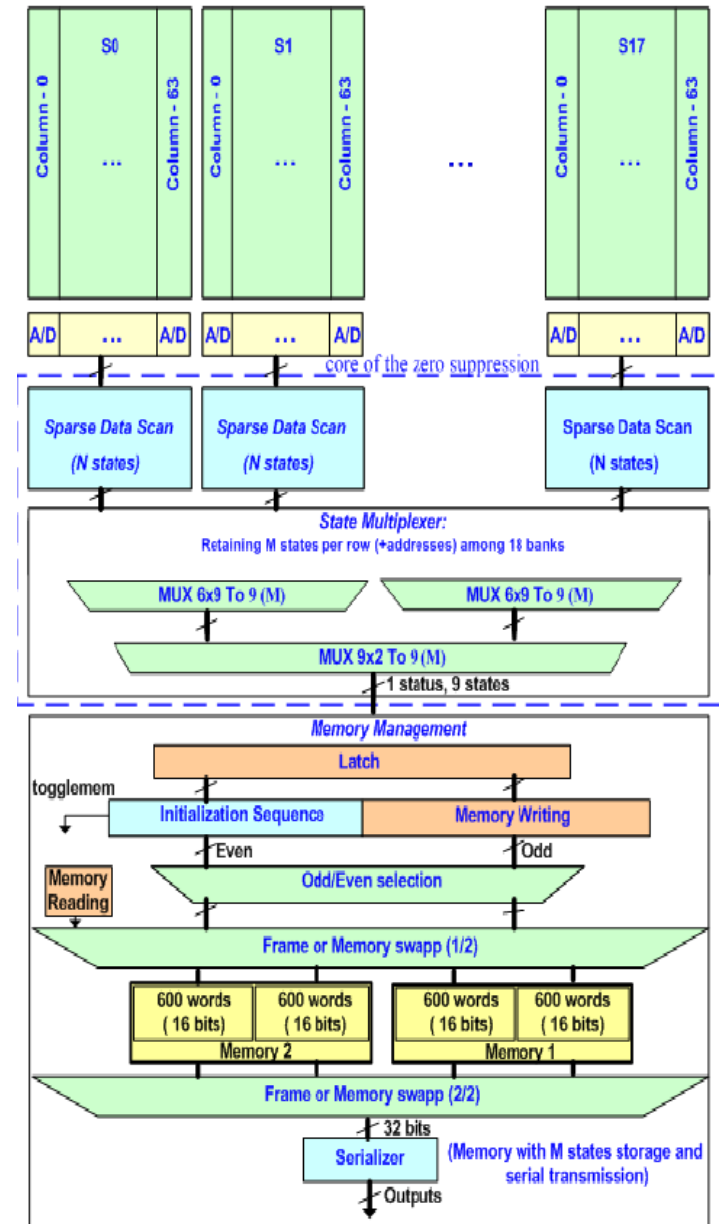
► Representation of hits in a matrix of pixels



► After AD conversion by discriminators



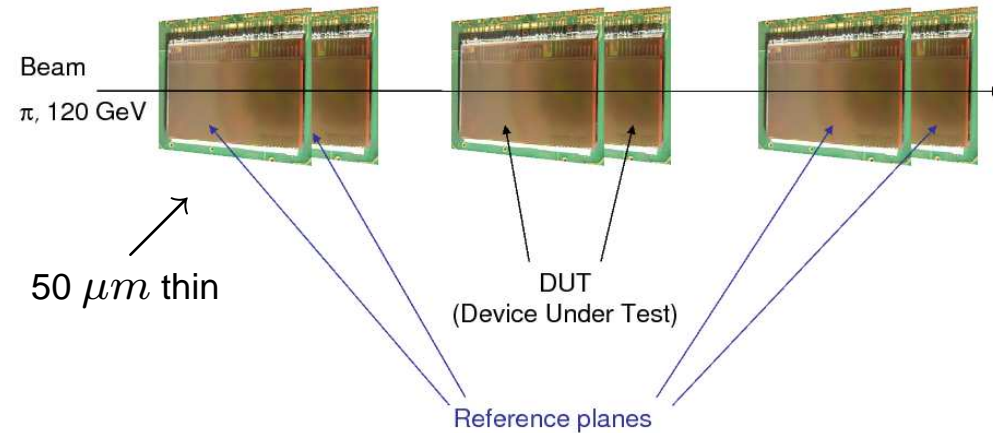
- Encoding limited to rows
⇒ no row to row correlation for clustering
- Same logic implemented in Ultimate



High-Resistivity CMOS Pixel Sensors

• M.i.p. detection with LOW & HIGH resistivity CMOS sensors combined in a Beam Telescope (BT)

- * 4 EUDET ref. sensors & 2 sensors under test
- * June 2010 at CERN-SPS (~ 120 GeV pions)
- * sensor variants : standard epitaxy ($14 \mu m$ thick)
& high-resistivity epitaxy (10 & $15 \mu m$ thick)



• Main Results:

- * det. eff. $\sim 100\%$ (SNR ~ 40) for very low fake rate:

▷ plateau until fake rate of few 10^{-6}

- * single point resolution $\lesssim 4 \mu m$

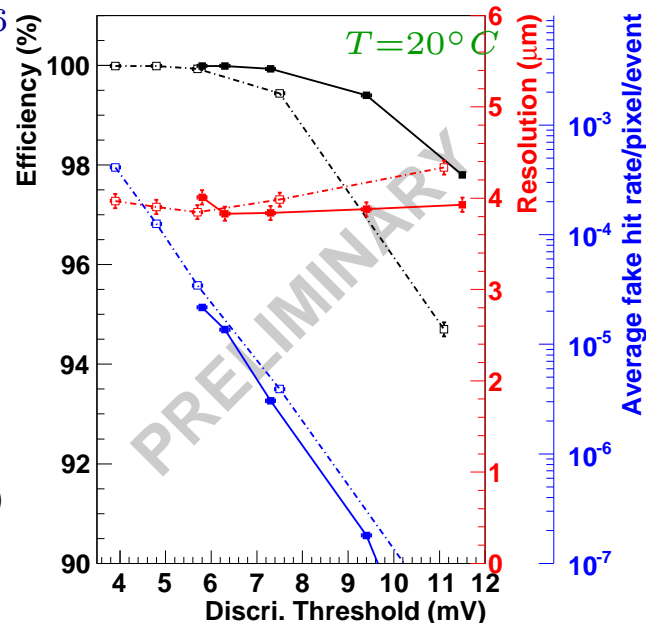
- * det. eff. still $\sim 100\%$ after exposure
to fluence of $1 \cdot 10^{13} n_{eq}/cm^2$

⇒ **Excellent detection performances**

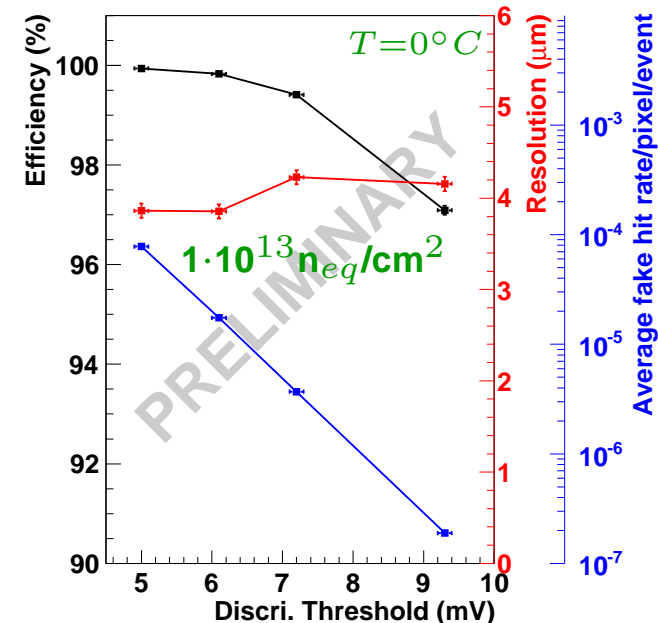
with high-resistivity epitaxial layer
despite moderate resistivity ($400 \Omega \cdot cm$)
and poor depletion voltage ($< 1 V$)

⇒ **Tolerance to $\gtrsim O(10^{14}) n_{eq}/cm^2$ seems within reach (study under way)**

Mi26 HR-15 and HR-10 Efficiency, Fake rate and Resolution

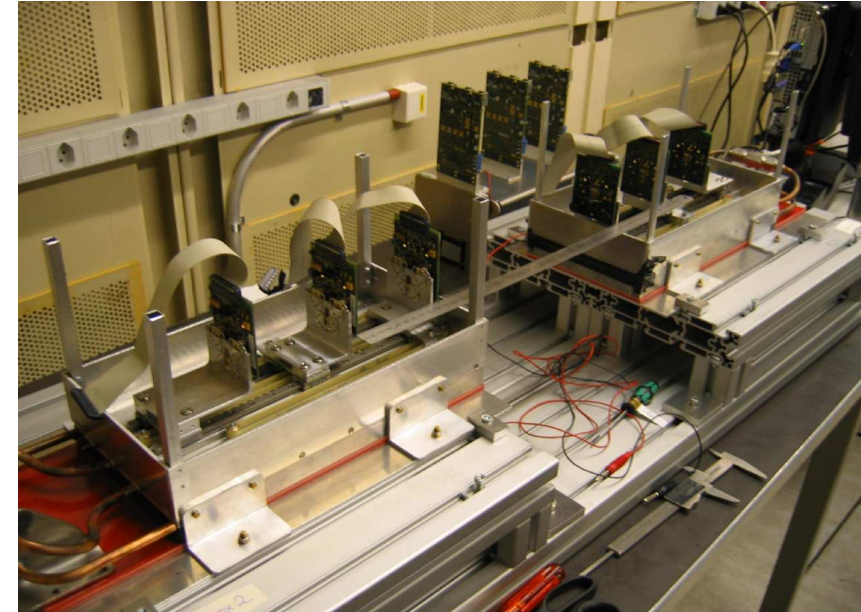


Mi26 HR-15 Efficiency, Fake rate and Resolution
for a chip irradiated with a $1.10^{13} n_{eq}$ dose at $T_{op} \sim 0^\circ C$



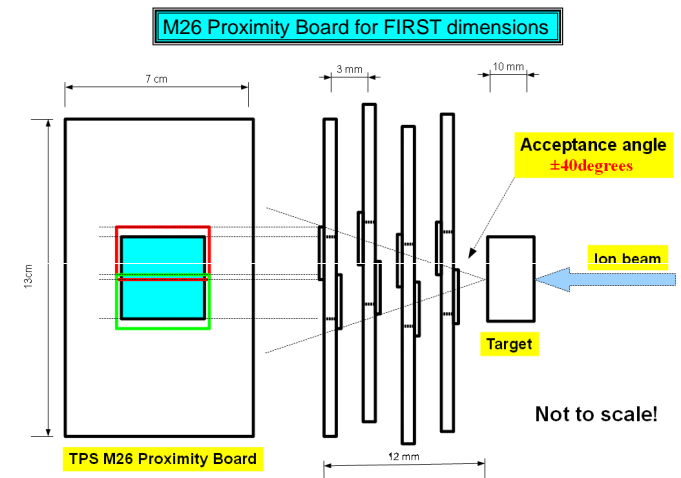
Direct Applications of MIMOSA-26

- Beam telescope of the FP6 project EUDET
 - ✧ 2 arms of 3 planes (plus 1-2 high resolution planes)
 - ✧ MIMOSA-26 thinned to $50 \mu m$
 - ✧ $\sigma_{extrapol.} \sim 1-2 \mu m$ EVEN with e^- (3 GeV, DESY)
 - ✧ frame read-out frequency $O(10^4)$ Hz
 - ✧ running since '07 (demonstrator: analog outputs)
at CERN-SPS & DESY (numerous users)



- Spin-offs :

- ✧ Several BT copies : foreseen for detector R&D
- ✧ BT for channelling studies, mass spectroscopy, etc.
- ✧ CBM (FAIR) : MVD demonstrator (2-sided layers) for CBM-MVD (HP-2 project)
- ✧ FIRST (GSI) : VD for hadrontherapy $d\sigma/d\Omega$ measurements ▷▷▷



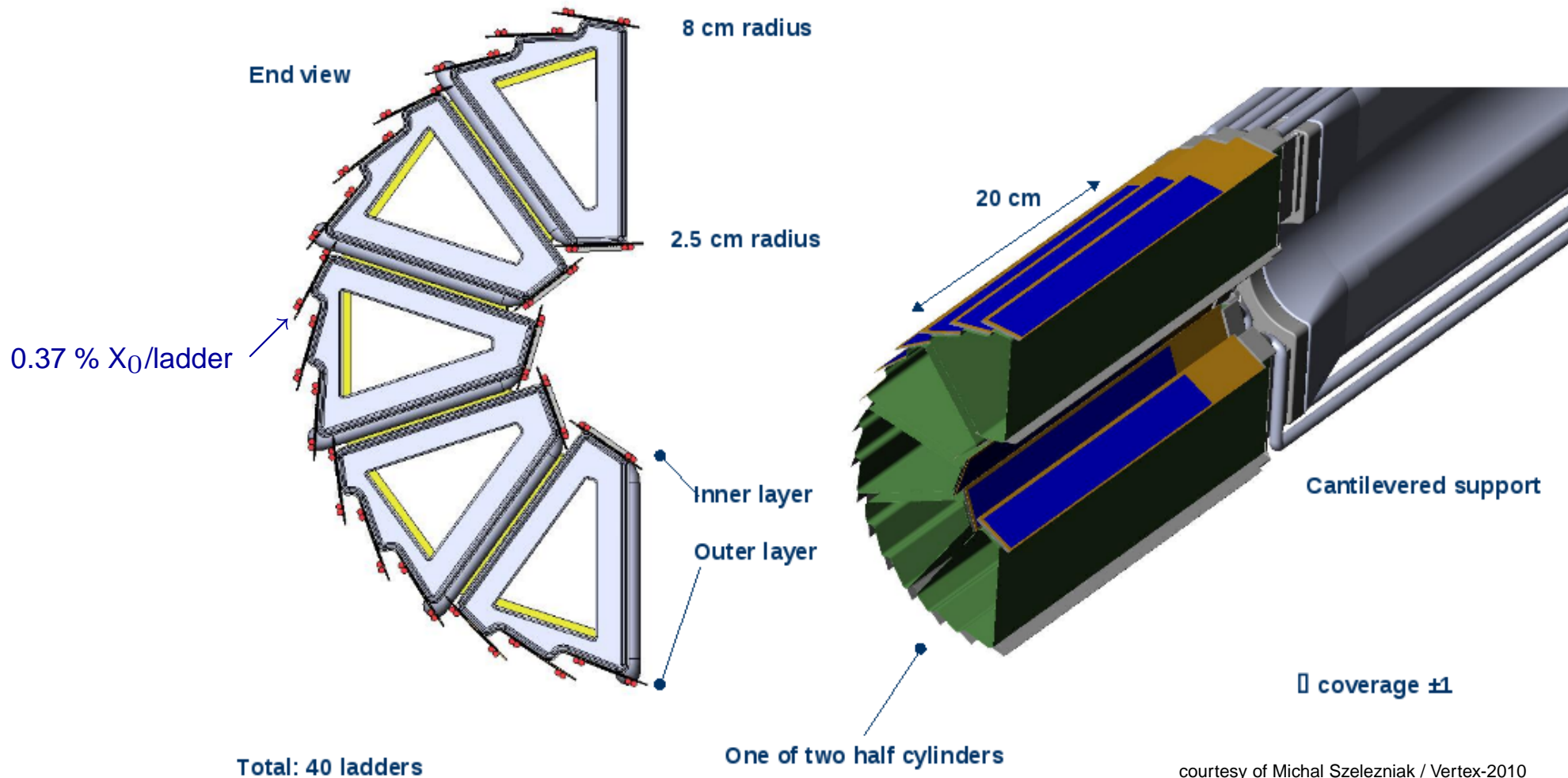
Eleuterio Spiriti

TPS meeting, March 2010

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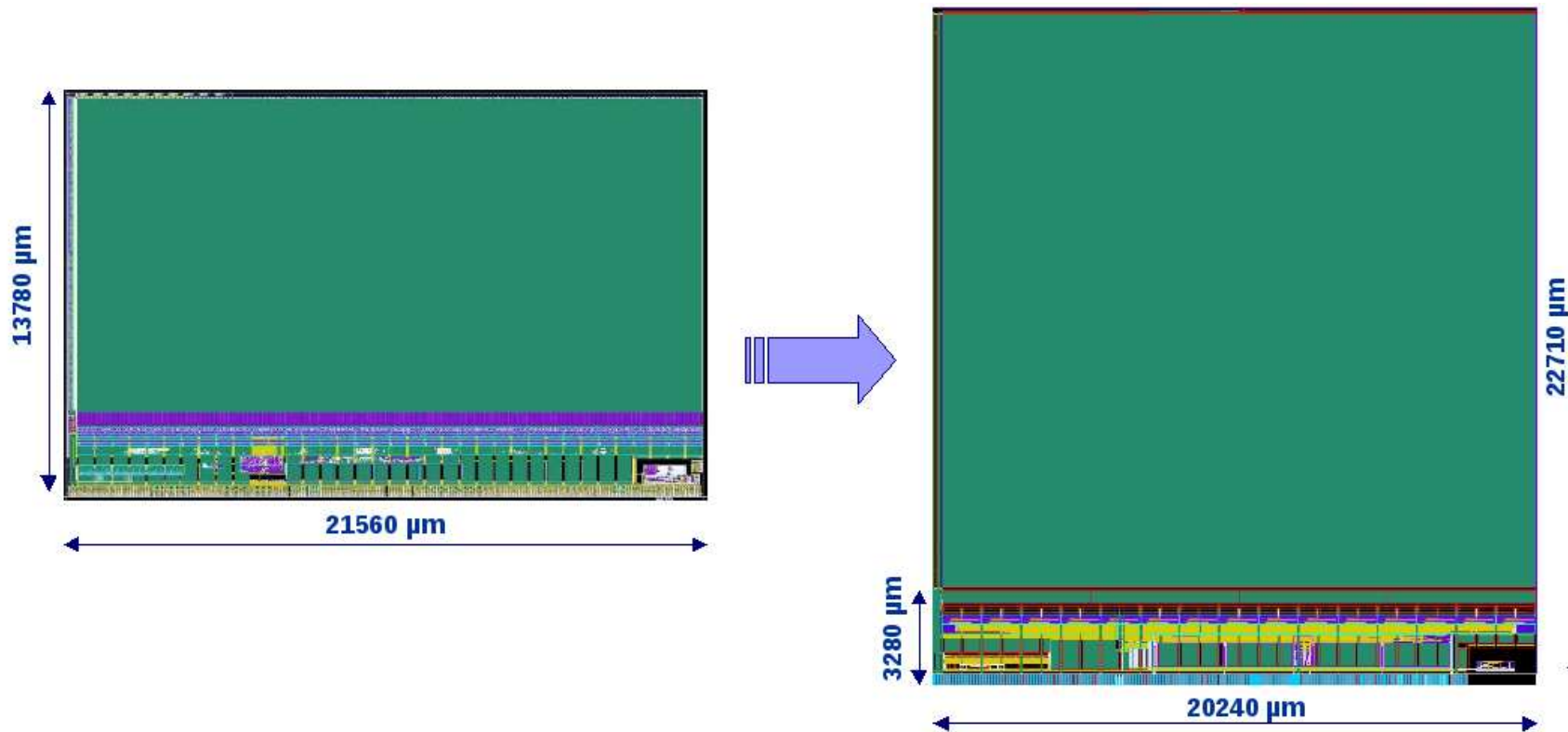
Application of CMOS sensors to the STAR-PXL

The detector ladders are 50 μm thinned silicon, on a flex kapton/aluminum cable.



▷▷▷ 1st vertex detector equipped with CMOS pixel sensors → 1st data taking in 2013

From MIMOSA-26 to ULTIMATE



- Half reticle 1152 x 567 pixel matrix
- Temperature ~20 °C
- Light power consumption constrains
- Space resolution ~4 μm
- No constrains on radiation tolerance

- Full reticle 960 x 928 pixel matrix
 - ↳ Longer integration time ~200 μs
- Temperature 30-35 °C
- Power consumption ~100 mW/cm²
- Space resolution < 10 μm
- 150 kRad / yr & few 10¹² Neq /cm² /yr

➔ **Optimisation**

courtesy of Ch. Hu-Guo / TWEPP-2010

MIMOSA-22AHR: Motivations, Properties, Tests Performed

● Motivations :

- ✧ validate larger pitch design \Rightarrow power dissipation
- ✧ try enhancing in-pixel amplification \Rightarrow sensitivity to discri. offset
- ✧ enhance radiation tolerance at 30°C
- ✧ explore and validate new epitaxial layers (AMS home made vs provider)

● Main components:

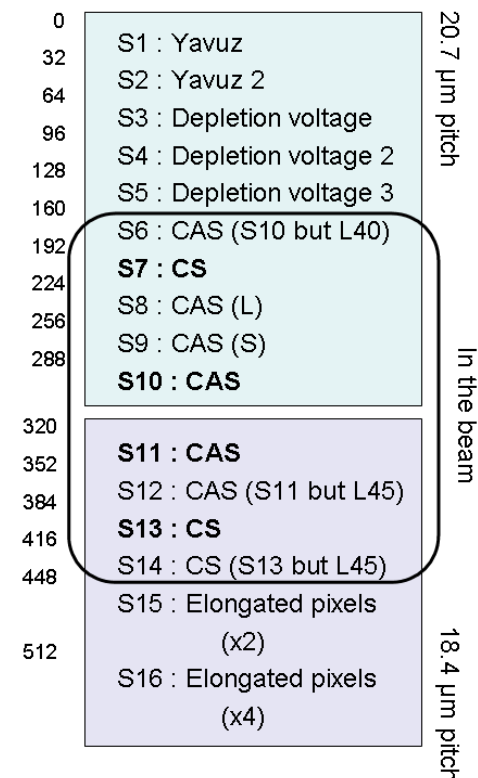
- ✧ pitch: 20.7 μm (UTIMATE) and 18.4 μm (MIMOSA-26)
- ✧ in-pixel amplification: Common Source & Cascode
- ✧ various features against ionising radiation damage: ETL, wide T gate
- ✧ features against non-ionising radiation damage: diode size, depletion potential

● Fabrication:

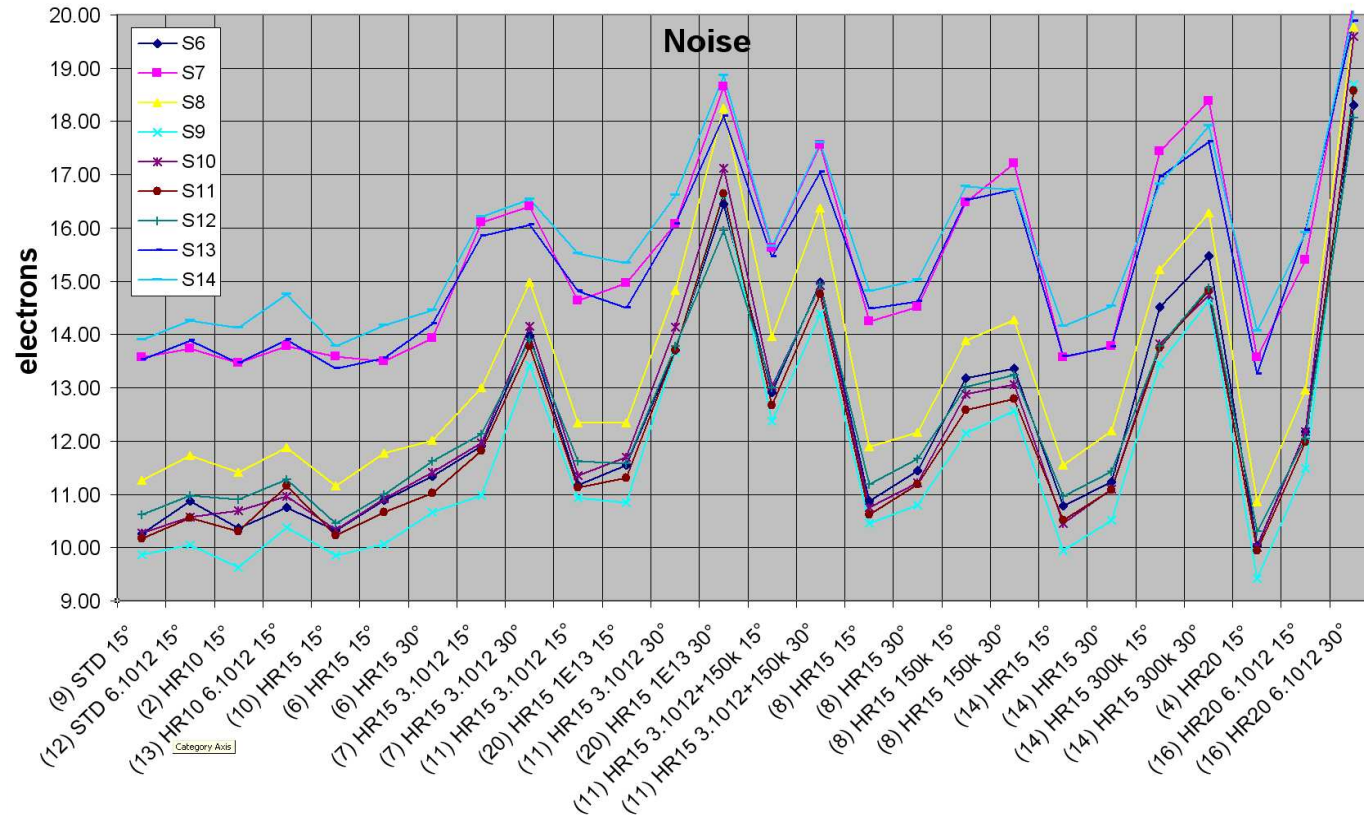
- ✧ part of an AMS-0.35 μm engineering run submitted in May 2010 \rightarrow back in July
- ✧ various epitaxial layers: standard (M-22 & M-26), HR-10 (M-26), HR-15 (AMS), HR-20 (AMS)

● Tests performed (mainly at 3.3 V):

- ✧ extensive lab tests: CCE (^{55}Fe), noise (fake rate) ✧ HR-15 and HR-10 tested at CERN-SPS (August & Sept. 2010)
- ✧ irradiation tolerance tests: 150 kRad, $3 \cdot 10^{12} n_{eq}/\text{cm}^2$ and combined ✧ temperature dependence: 20°C and 30°C
- ✧ "STAR running conditions": 150 kRad \oplus $3 \cdot 10^{12} n_{eq}/\text{cm}^2$ \oplus 30°C \oplus 75 MHz (should have been 50 MHz)



MIMOSA-22AHR: Noise Performance



MIMOSA-22AHR: Performances before Irradiation

- Tests performed at CERN-SPS:

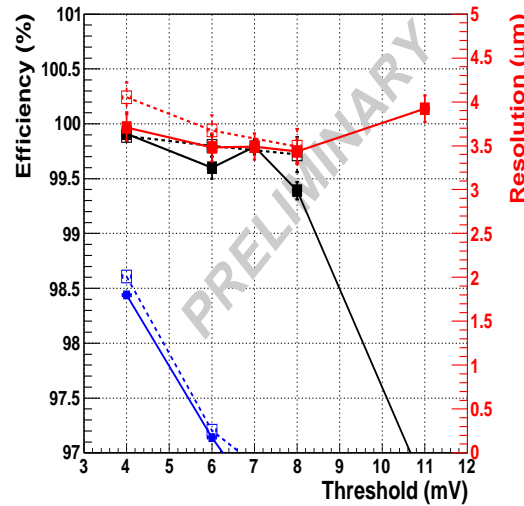
- * sensor mounted on beam telescope (4 pairs of Si-strip detectors)
- * vary discriminator threshold (JTAG), temperature, clock frequency
- * measure detection efficiency, fake hit rate, single point resolution

- Results for 20.7 μm pitch pixels \triangleright mV-SNR equivalence at 30 $^{\circ}$ C

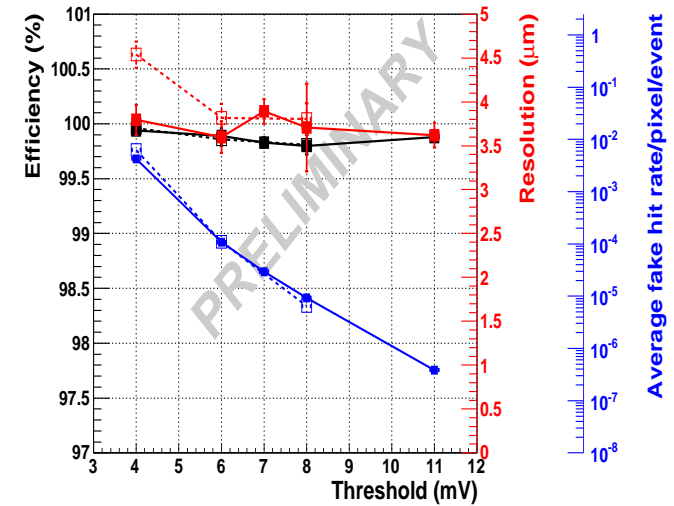
Threshold \triangleright	4 mV	6 mV	8 mV
S7	4.1	6.4	8.7
S10	2.5	4.2	5.9
S6	2.7	4.4	6.1
S8	2.5	4.2	5.9

- Typical noise performance : 12-14 e^{-} ENC

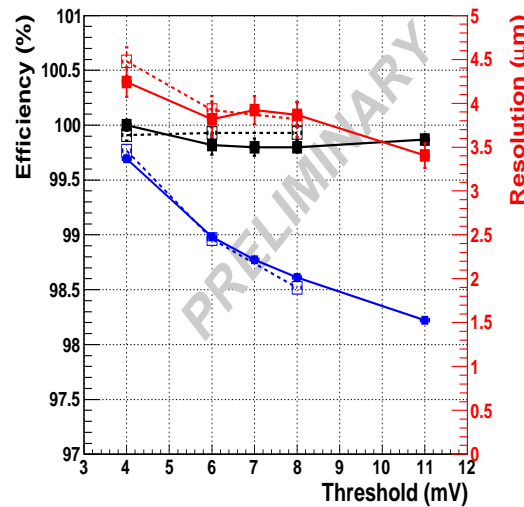
S7 (CS)



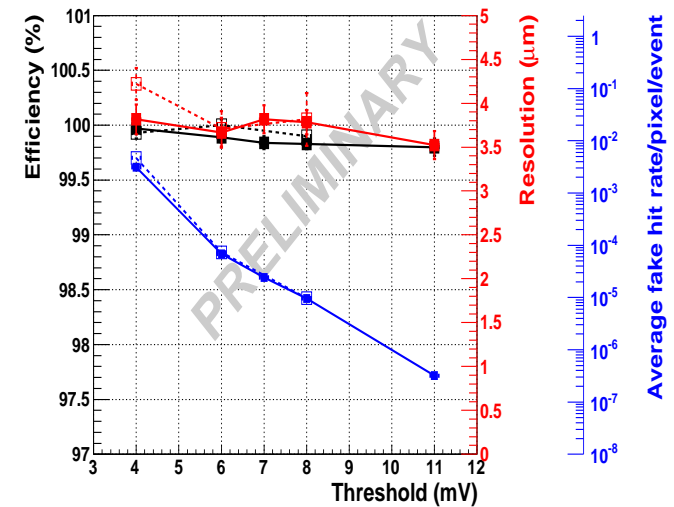
S10 (CAS)



S8 (CAS large diode)



S6 (CAS)



MIMOSA-22AHR: Performances before Irradiation

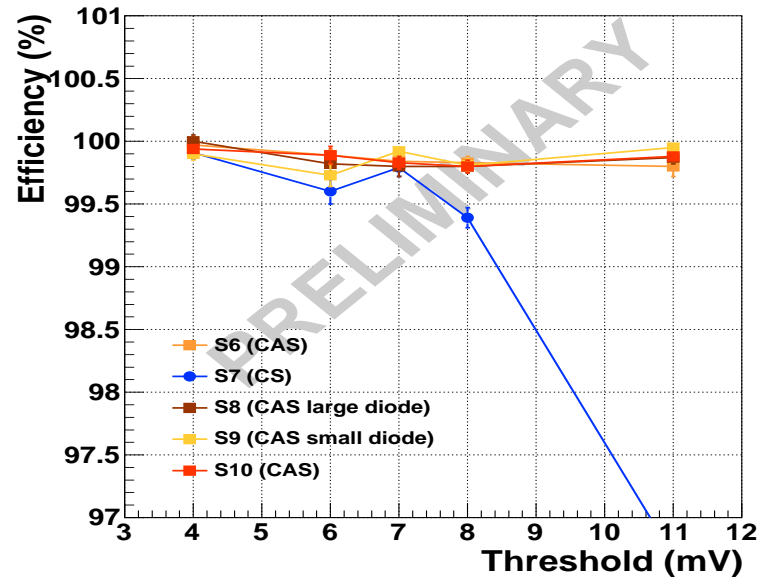
- Efficiency vs fake hit rate:

- ✧ define threshold values allowing high detection efficiency and low fake rate
- ⇒ keep fake rate $\lesssim 10^{-4}$

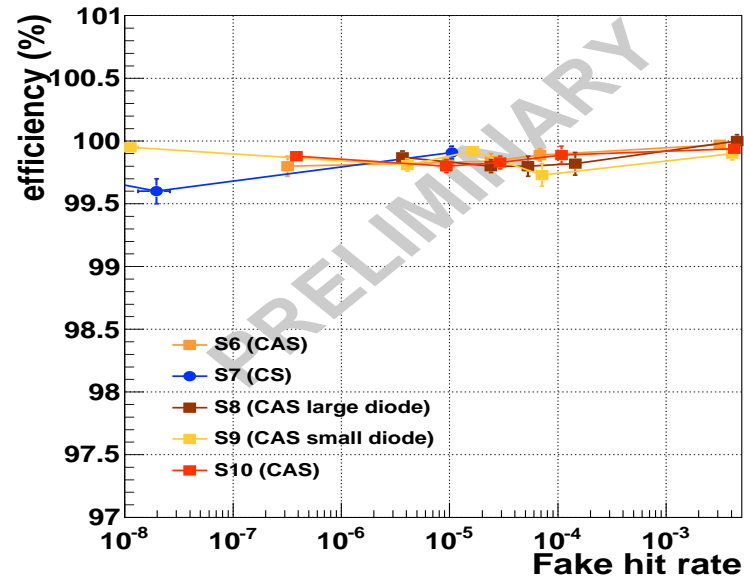
- Results for 20.7 μm pitch pixels \triangleright
mV-SNR equivalence at 30°C

Threshold \triangleright	4 mV	6 mV	8 mV
S7	4.1	6.4	8.7
S10	2.5	4.2	5.9
S6	2.7	4.4	6.1
S8	2.5	4.2	5.9

Efficiency vs Threshold



Efficiency vs Fake hit rate



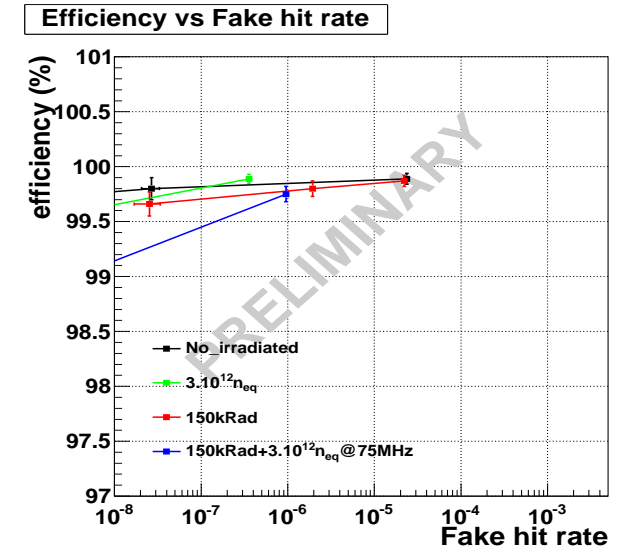
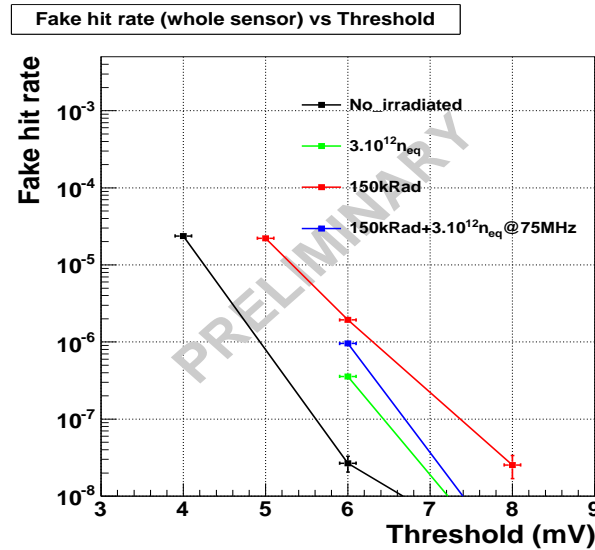
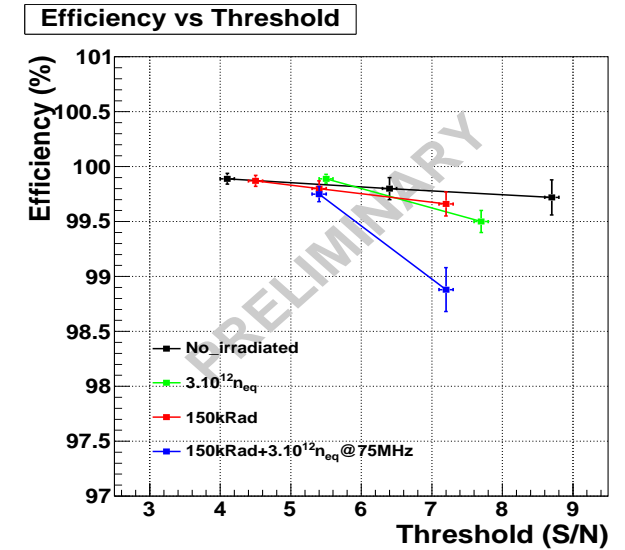
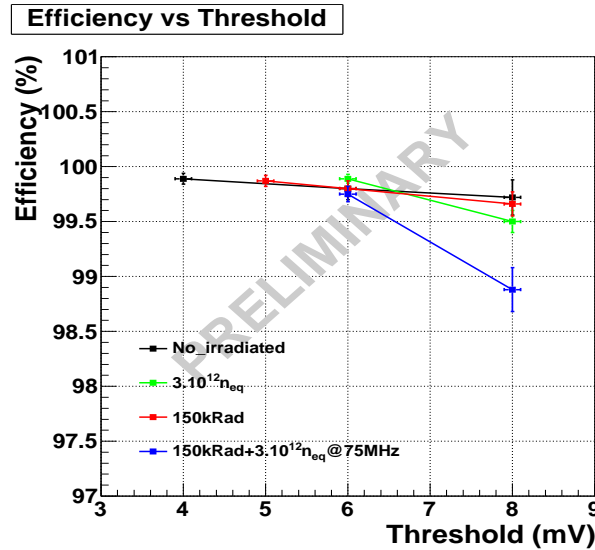
MIMOSA-22AHR S7 Pixel : Summary

- Summary of results obtained with S7 (CS) :

- * evolution of detection efficiency
- * evolution of fake hit rate
- ↪ look for viable working point

- Results for 20.7 μm pitch pixels \triangleright
mV-SNR equivalence at 30°C

Threshold (mV) \triangleright	4	5	6	8
before irradi.	4.1		6.4	8.7
$3 \cdot 10^{12} \text{ n}_{eq}/\text{cm}^2$			5.5	7.7
150 kRad		4.5	5.4	7.2
combined (75 MHz)			5.2	6.9



⇒ No problem to find a threshold where the detection efficiency is $> 99.5\%$ while the fake hit rate remains negligible

MIMOSA-22AHR S10 Pixel : Summary

- Summary of results obtained with S10 (CAS) :

- ✳ evolution of detection efficiency

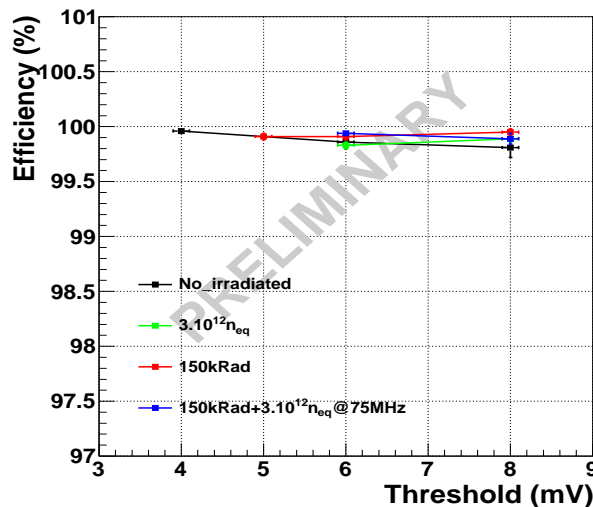
- ✳ evolution of fake hit rate

- ↪ look for viable working point

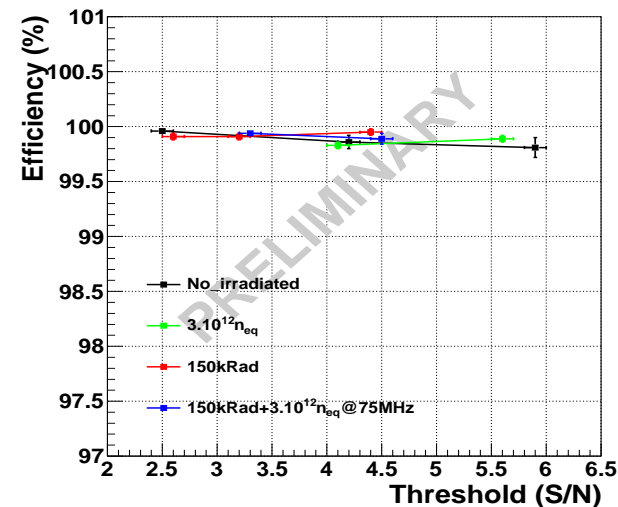
- Results for 20.7 μm pitch pixels \triangleright
mV-SNR equivalence at 30°C

Threshold (mV) \triangleright	4	5	6	8
before irradi.	2.5		4.2	5.9
$3 \cdot 10^{12} \text{ n}_{eq}/\text{cm}^2$			4.1	5.6
150 kRad		2.6	3.2	4.4
combined (75 MHz)			3.2	4.3

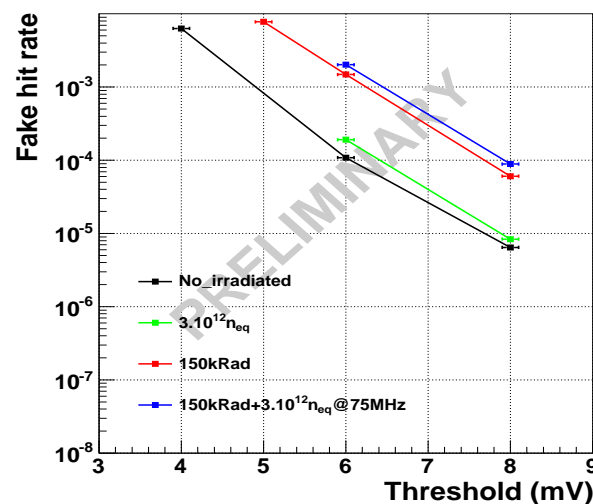
Efficiency vs Threshold



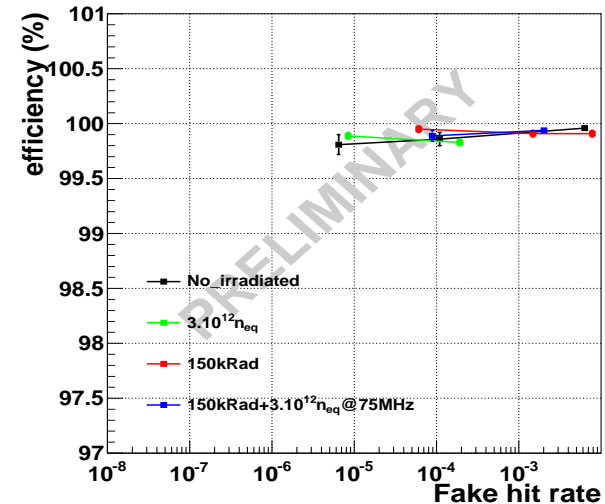
Efficiency vs Threshold



Fake hit rate (whole sensor) vs Threshold



Efficiency vs Fake hit rate

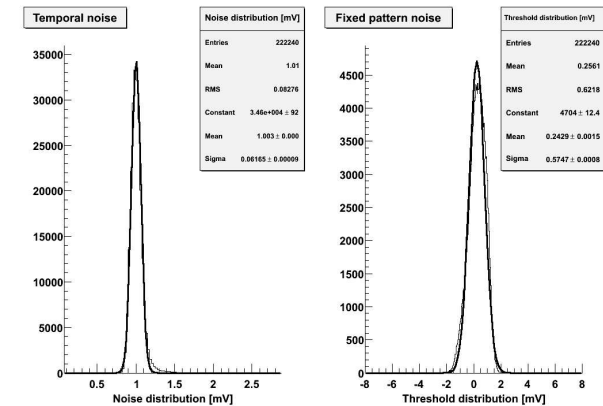
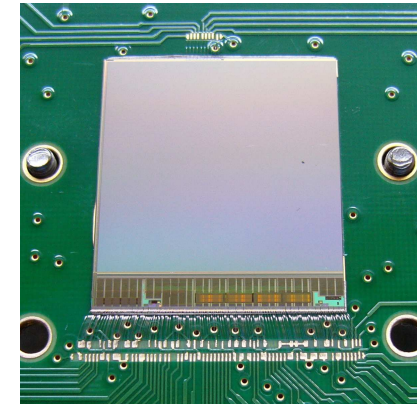


⇒ No problem to find a threshold where the detection efficiency is $> 99.5\%$ while the fake hit rate remains negligible

STAR-PXL Detector : MIMOSA-28

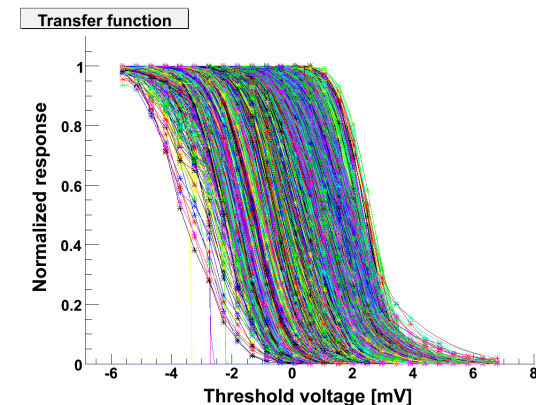
● Main characteristics of ULTIMATE:

- * 0.35 μm process with high-resistivity epitaxial layer
- * column // architecture with in-pixel cDS & amplification
- * end-of-column discrimination and binary charge encoding, followed by \emptyset
- * active area: 960 columns of 928 pixels ($19.9 \times 19.2 \text{ mm}^2$)
- * pitch: 20.7 $\mu m \rightarrow \sim 0.9$ million pixels
 - \hookrightarrow charge sharing $\Rightarrow \sigma_{sp} \sim 3.5 \mu m$ expected
- * $t_{r.o.} \lesssim 200 \mu s$ ($\sim 5 \times 10^3$ frames/s)
 - \Rightarrow suited to $> 10^6$ part./cm²/s
- * 2 outputs at 160 MHz
- * $\lesssim 150 \text{ mW/cm}^2$ power consumption



▷▷▷ Chip back from foundry \Rightarrow lab tests under way since early April :

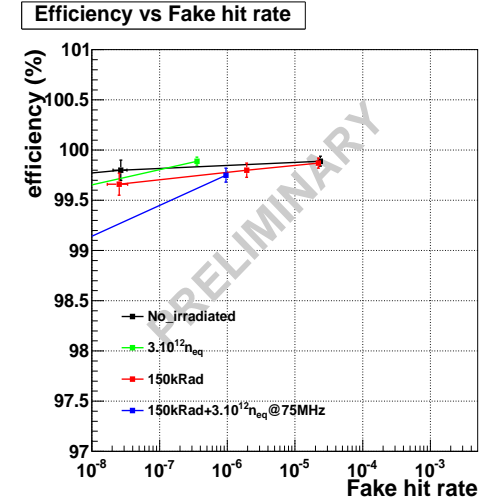
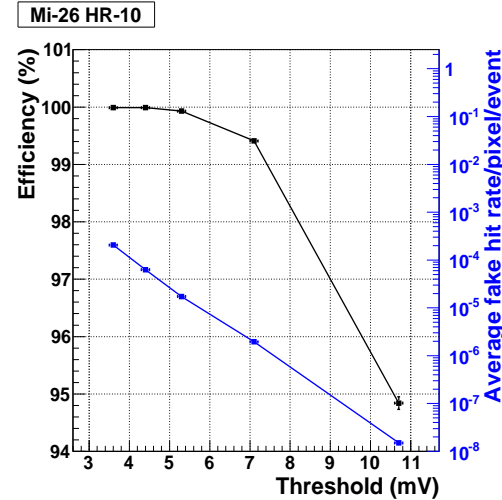
- * $N \lesssim 15 \text{ e}^- \text{ ENC}$ at 30-35°C (as MIMOSA-22AHR)
- * CCE (^{55}Fe) similar to MIMOSA-22AHR
- **m.i.p. detection assessment at CERN-SPS in June-July '11**
- radiation tolerance assessment through Spring and Summer



Expected M.I.P. Detection Performances of MIMOSA-28

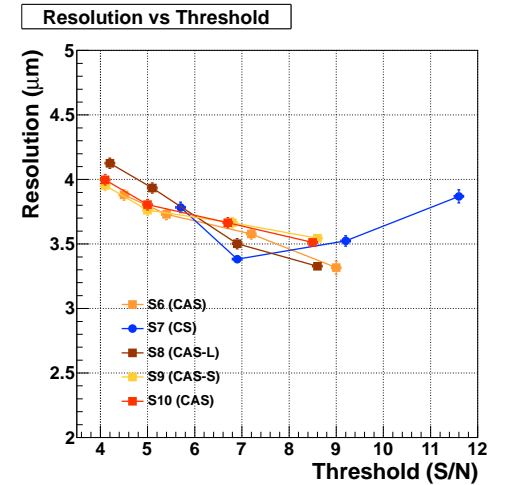
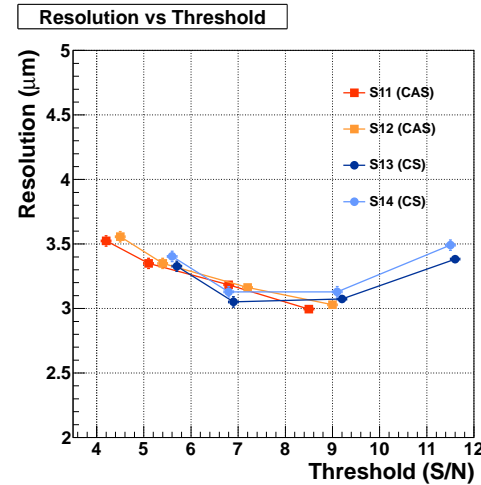
- Expected m.i.p. detection performances determined with MIMOSA-26 and with medium size MIMOSA-22AHR prototype of ULTIMATE/M28 at SPS with $\sim 100 \text{ GeV } \pi^-$ (Summer '10)

- Detection efficiency vs fake hit rate :
sensor works with high detection efficiency and marginal contamination by noise fluctuations (fake hits)



- Single point resolution :

- * 18.4 μm pitch (MIMOSA-26) $\rightarrow \sigma_{sp} \sim 3 \mu m$
- * 20.7 μm pitch (ULTIMATE) $\rightarrow \sigma_{sp} \sim 3.5 \mu m$



SUMMARY

- The translation from MIMOSA-26 to ULTIMATE/Mimo-28 completed
 - ↳ in time for data taking in FY 2014
- Sensors were fabricated and are being tested :
 - ✧ lab tests before irradiation show expected behaviour
 - ✧ irradiation tests under way: 150 kRad and $3 \cdot 10^{12} n_{eq}/cm^2$
 - ✧ mip detection performance assessment: beam tests at CERN-SPS in June/July
- Pending question : should the digital circuitry be made latch-up free ?
- ULTIMATE acts as an important forerunner for several sensors of upcoming vertex detectors